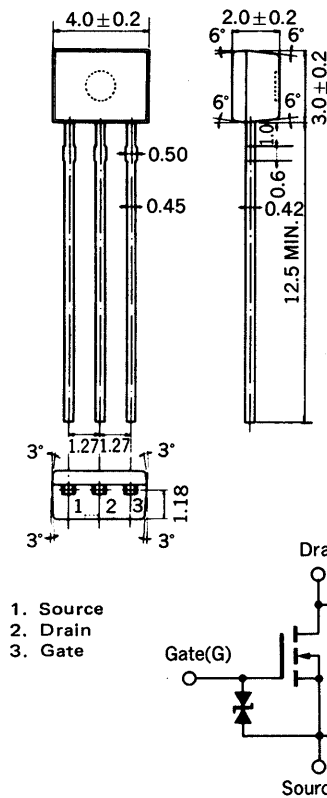


# MOS FIELD EFFECT TRANSISTOR 2SK1132

## N-CHANNEL MOS FET FOR HIGH SPEED SWITCHING

### PACKAGE DIMENSIONS (Unit : mm)



1. Source
2. Drain
3. Gate

(Diode in the figure is the parasitic diode.)

The 2SK1132, N-channel vertical type MOS FET, is a switching device which can be driven directly by the output of ICs having a 5 V power source.

The MOS FET has excellent switching characteristics and is suitable for use as a high-speed switching device in digital circuits.

### FEATURES

- Directly driven by ICs having a 5 V power source.
- Not necessary to consider driving current because of its high input impedance.
- Possible to reduce the number of parts by omitting the bias resistor.
- Can be replaced with any resistor self-contained type transistor.
- Can be used complementarily with the 2SJ165.

### QUALITY GRADE

Standard

Please refer to "Quality grade on NEC Semiconductor Devices" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

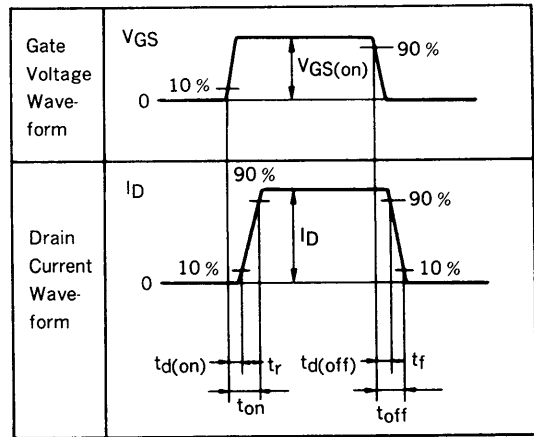
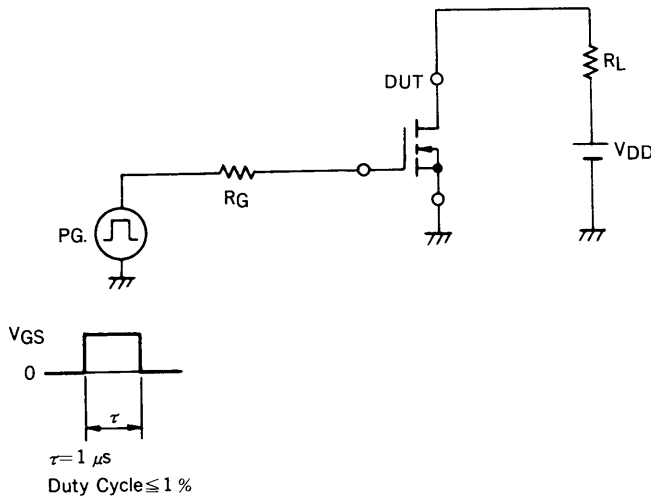
### ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

PARAMETER	SYMBOL	RATINGS	UNIT	TEST CONDITIONS
Drain to Source Voltage	$V_{DSS}$	50	V	$V_{GS} = 0$
Gate to Source Voltage	$V_{GSS}$	$\pm 7.0$	V	$V_{DS} = 0$
Drain Current	$I_D(\text{DC})$	$\pm 100$	mA	
Drain Current	$I_D(\text{pulse})$	$\pm 200$	mA	$PW \leq 10 \text{ ms}$ , Duty Cycle $\leq 50 \%$
Total Power Dissipation	$P_T$	250	mW	
Channel Temperature	$T_{ch}$	150	$^\circ\text{C}$	
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$	

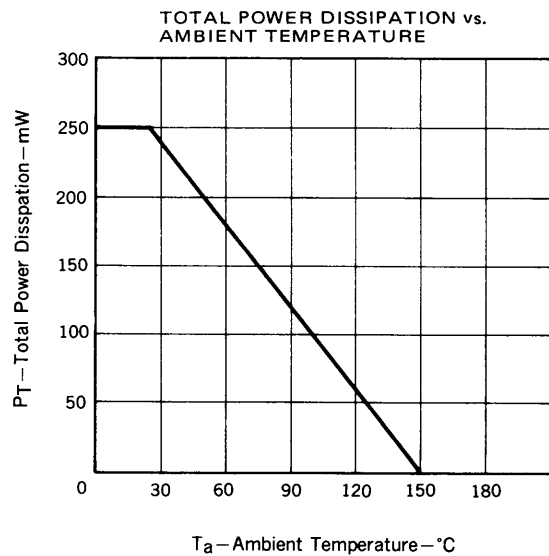
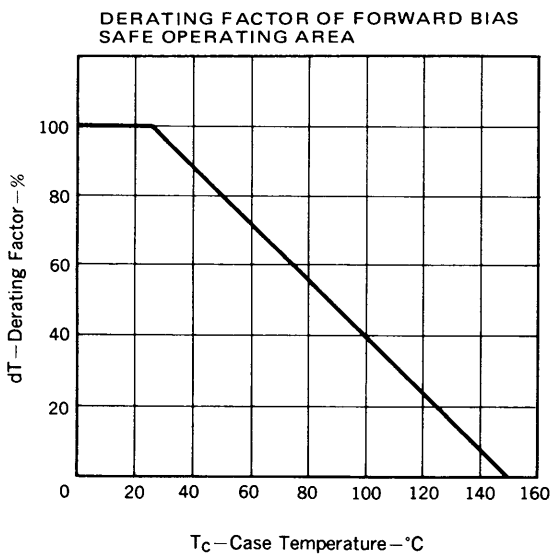
ELECTRICAL CHARACTERISTICS (T<sub>a</sub> = 25 °C)

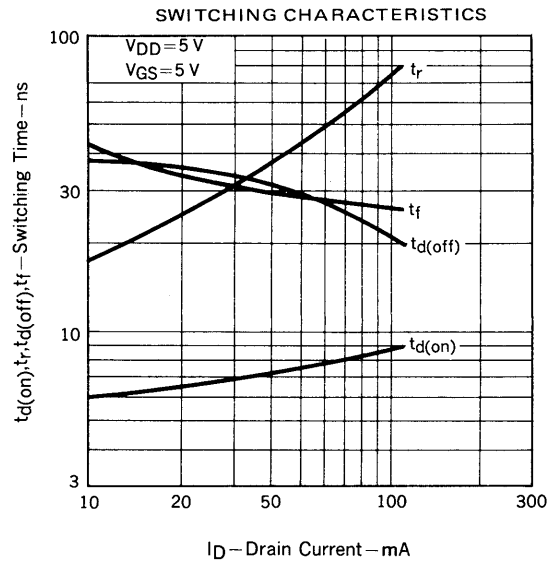
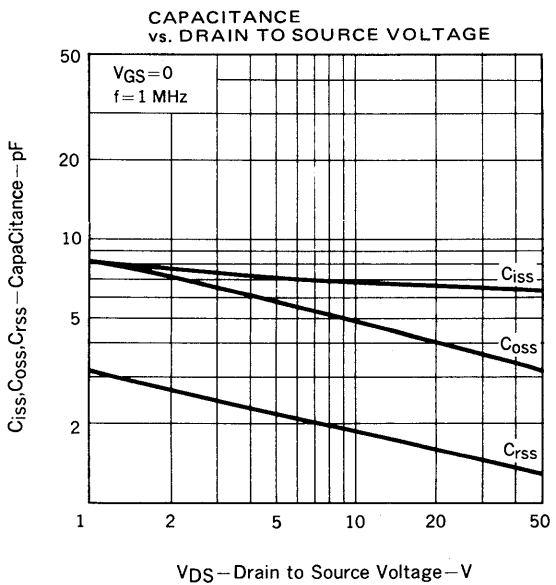
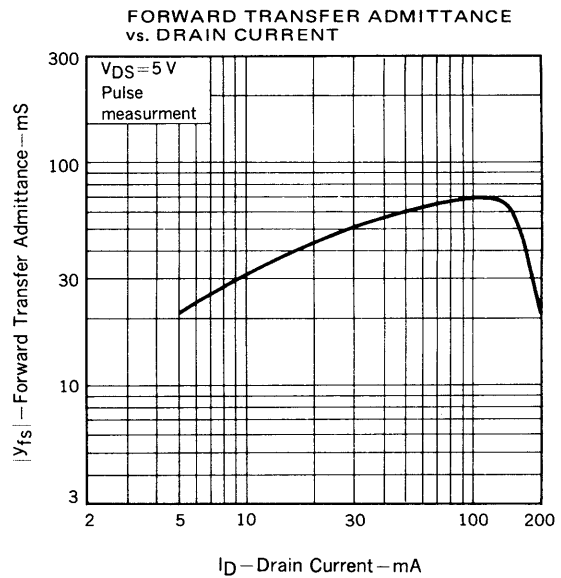
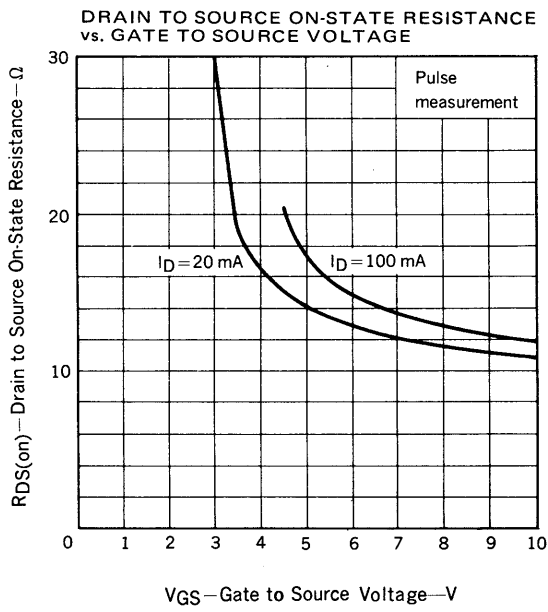
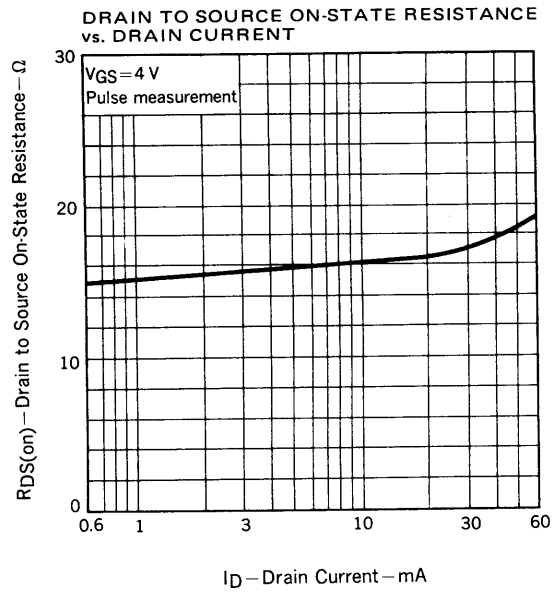
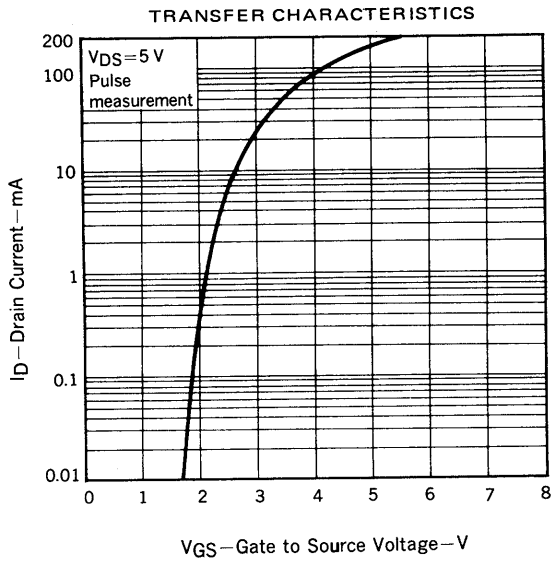
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Drain Cut-off Current	I <sub>DSS</sub>			10	μA	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 0
Gate Leakage Current	I <sub>GSS</sub>			±10	μA	V <sub>GS</sub> = ±7 V, V <sub>DS</sub> = 0
Gate Cut-off Voltage	V <sub>GS(off)</sub>	1.0	1.7	2.0	V	V <sub>DS</sub> = 5.0 V, I <sub>D</sub> = 1.0 μA
Forward Transfer Admittance	y <sub>fs</sub>	20	40		mS	V <sub>DS</sub> = 5.0 V, I <sub>D</sub> = 20 mA
Drain to Source On-State Resistance	R <sub>DS(on)</sub>		16	50	Ω	V <sub>GS</sub> = 4.0 V, I <sub>D</sub> = 20 mA
Input Capacitance	C <sub>iss</sub>		7		pF	V <sub>DS</sub> = 5.0 V, V <sub>GS</sub> = 0, f = 1 MHz
Output Capacitance	C <sub>oss</sub>		6		pF	
Feedback Capacitance	C <sub>rss</sub>		2		pF	
Turn-On Delay Time	t <sub>d(on)</sub>		6		ns	V <sub>GS(on)</sub> = 5.0 V, R <sub>G</sub> = 10 Ω V <sub>DD</sub> = 5.0 V, I <sub>D</sub> = 20 mA R <sub>L</sub> = 250 Ω
Rise Time	t <sub>r</sub>		25		ns	
Turn-Off Delay Time	t <sub>d(off)</sub>		36		ns	
Fall Time	t <sub>f</sub>		35		ns	

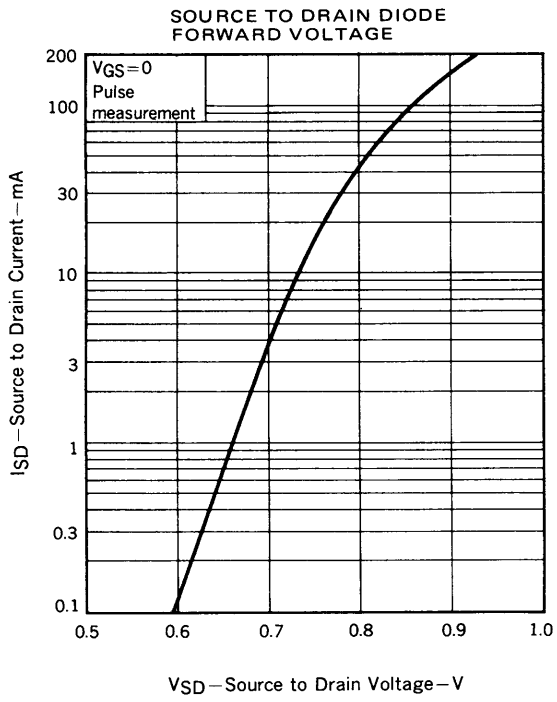
SWITCHING TIME MEASUREMENT CIRCUIT AND CONDITIONS



TYPICAL CHARACTERISTICS (T<sub>a</sub> = 25 °C)







**RECOMMENDED SOLDERING CONDITIONS**

Solder this product under the following recommended conditions.

For soldering methods or soldering conditions other than those recommended in the table, please consult our NEC salespeople.

**Insert type**

Soldering method	Soldering conditions	Recommended condition code
Wave soldering	Solder bath temperature: 260 °C max. Soldering time: 10 sec max.	

[MEMO]

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The devices listed in this document are not suitable for use in the field where very high reliability is required including, but not limited to, aerospace equipment, submarine cables, nuclear reactor control systems and life support systems. If customers intend to use NEC devices for above applications or those intended to use "Standard", or "Special" quality grade NEC devices for the applications not intended by NEC, please contact our sales people in advance.

Application examples recommended by NEC Corporation

Standard: Data processing and office equipment, Communication equipment (terminal, mobile). Test and Measurement equipment, Audio and Video equipment, Other consumer products, etc.

Special: Automotive and Transportation equipment, Communication equipment (trunk line), Train and Traffic control devices, industrial robots, Burning control systems, antidisaster systems, anticrime systems etc.



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